

ZENER DIODE

- Monolithic Temperature Compensated Zener Reference Chips
- All Junctions Completely Protected with Silicon Dioxide
- Electrically Equivalent to 1N821 Thru 1N829
- Compatible with all Wire Bonding and Die Attach Techniques with the Exception of Solder Reflow

DEVICES

CD821 thru CD829A

QUALIFIED LEVELS

**JANHC
JANKC**

MAXIMUM RATING AT 25°C

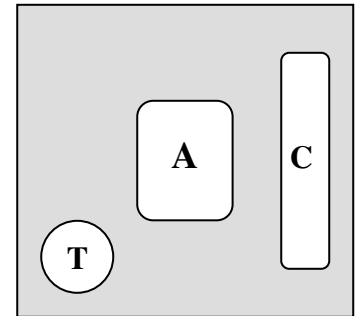
Operating Temperature: -65°C to +175°C
 Storage Temperature: -65°C to +175°C

REVERSE LEAKAGE CURRENT

$I_R = 2\mu A$ @ 25°C & $V_R = 3V_{dc}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$, unless otherwise specified)

| TYPE NUMBER | ZENER VOLTAGE | ZENER TEST CURRENT | MAXIMUM ZENER IMPEDANCE | -55° to +100° VOLTAGE TEMPERATURE STABILITY | EFFECTIVE TEMPERATURE COEFFICIENT |
|-------------|-------------------|--------------------|-------------------------|---|-----------------------------------|
| | $V_{ZT} @ I_{ZT}$ | I_{ZT} | Z_{ZT} (Note 1) | ${}^3V_{ZT}$ (Note 2) | |
| | VOLTS | mA | OHMS | mV | % / °C |
| CD821 | 5.9 – 6.5 | 7.5 | 15 | 96 | 0.01 |
| CD821A | 5.9 – 6.5 | 7.5 | 13 | 96 | 0.01 |
| CD823 | 5.9 – 6.5 | 7.5 | 15 | 48 | 0.005 |
| CD823A | 5.9 – 6.5 | 7.5 | 13 | 48 | 0.005 |
| CD825 | 5.9 – 6.5 | 7.5 | 15 | 19 | 0.002 |
| CD825A | 5.9 – 6.5 | 7.5 | 13 | 19 | 0.002 |
| CD826 | 5.9 – 6.5 | 7.5 | 15 | 20 | 0.002 |
| CD827 | 5.9 – 6.5 | 7.5 | 15 | 9 | 0.001 |
| CD827A | 5.9 – 6.5 | 7.5 | 13 | 9 | 0.001 |
| CD828 | 6.2 – 6.9 | 7.5 | 15 | 10 | 0.001 |
| CD829 | 5.9 – 6.5 | 7.5 | 15 | 5 | 0.0005 |
| CD829A | 5.9 – 6.5 | 7.5 | 13 | 5 | 0.0005 |



NOTE:

1. Zener impedance is derived by superimposing on I_{ZT} A 60Hz rms a.c. current equal to 10% of I_{ZT} .
2. The maximum allowable change observed over the entire temperature range i.e., the diode voltage will not exceed the specified mV at any discrete temperature between the established limits, per JEDEC standard No.5

TYPICAL CHANGE OF TEMPERATURE COEFFICIENT WITH CHANGE IN OPERATING CURRENT

Qualified per MIL-PRF-19500/159

CD821 thru CD829A

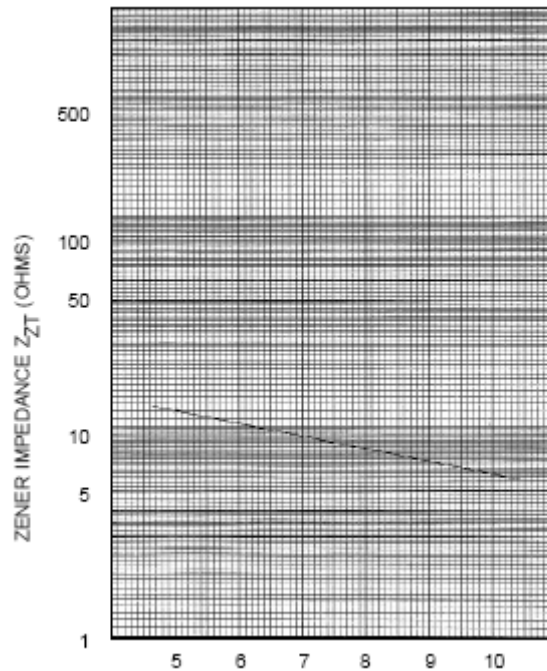


FIGURE 3
ZENER IMPEDANCE
VS.
OPERATING CURRENT

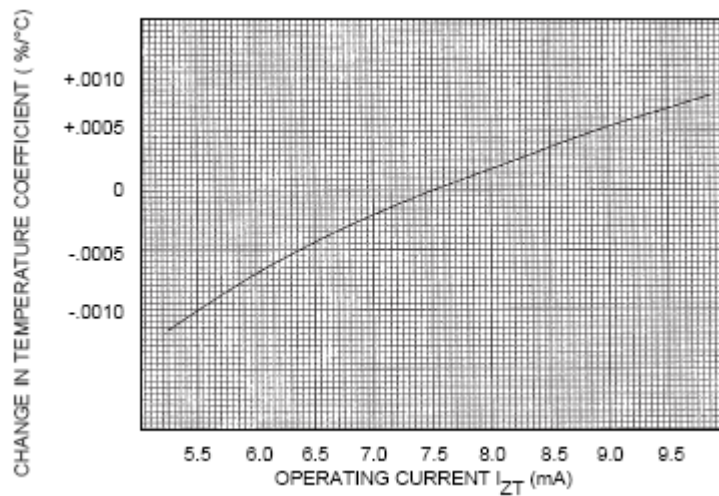
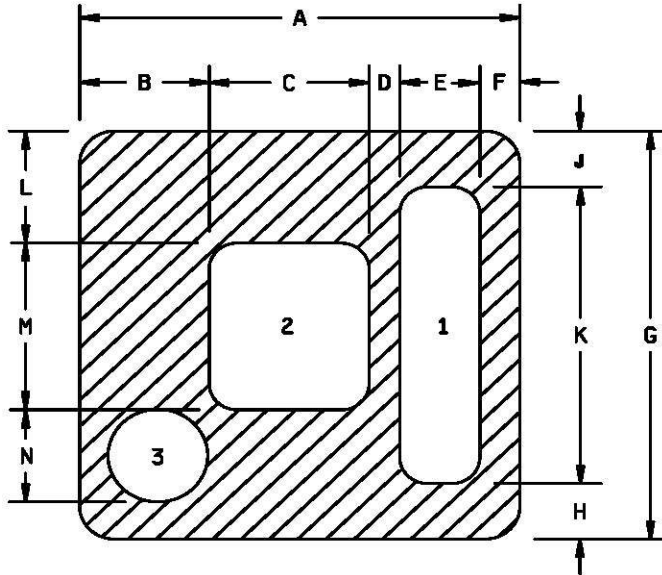


FIGURE 4

PACKAGE DIMENSIONS



| Symbol | Dimensions | | | |
|--------|------------|-------|-------------|------|
| | Inches | | Millimeters | |
| | Min | Max | Min | Max |
| A | .0280 | .0320 | .711 | .813 |
| B | .0080 | .0100 | .203 | .254 |
| C | .0104 | .0106 | .264 | .269 |
| D | .0019 | .0021 | .048 | .053 |
| E | .0054 | .0056 | .137 | .142 |
| F | .0020 | .0040 | .050 | .102 |
| G | .0280 | .0320 | .711 | .813 |
| H | .0030 | .0050 | .076 | .127 |
| J | .0030 | .0050 | .076 | .127 |
| K | .0209 | .0211 | .531 | .536 |
| L | .0080 | .0100 | .203 | .254 |
| M | .0104 | .0106 | .264 | .269 |
| N | .0059 | .0061 | .150 | .155 |

Backside must be electrically isolated to ensure proper performance.

DESIGN DATA

Metallization:

Top: 1 (Cathode) Al Circuit layout data:
 2 (Anode) Al For zener operation, cathode must be operated positive with respect to anode.
 3 (Test pad) Al Test pad is for wire bond evaluation only. No electrical contact is made with test pad.

Back: Au

Al thickness 25,000Å minimum.
 Gold thickness 4,000Å minimum.
 Chip thickness .010 inch (0.25 mm) ±0.002 inch (+0.05 mm).

NOTES:

1. Dimensions are in inches unless otherwise indicated.
2. Millimeters are given for general information only.
3. In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.

JANHC and JANKC (A-version) die dimensions.